Standard specifications of 100 mm β-Ga_2O_3 epitaxial wafer (by HVPE)

Epitaxial layer

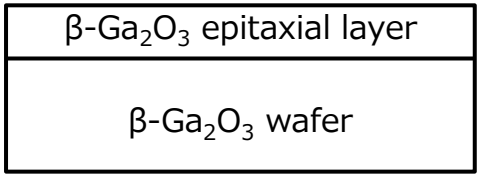
Items	Specifications
Dopant	Si+Cl[*1] (n-type)
Doping concentration (cm^{-3})	1×10^{16}
Thickness (μm) *Selectable in 1 μm increments.	5–10

*1: Unintentionally-doped

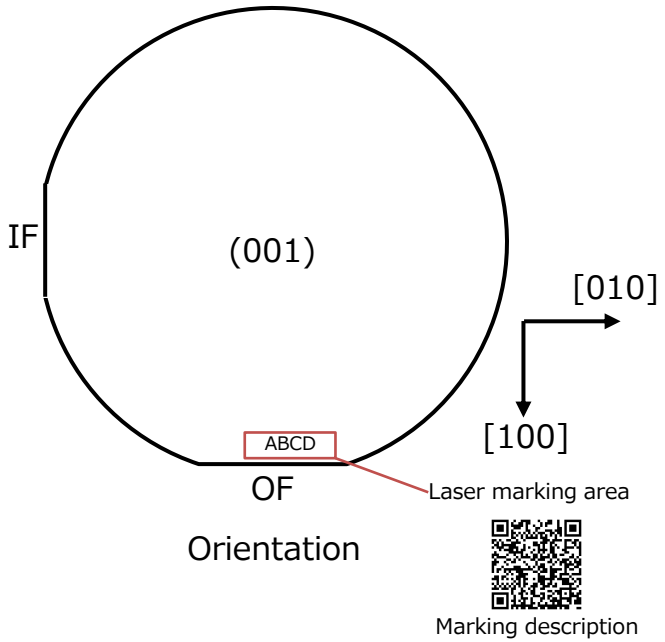
Epi-Wafer

Items	Specifications
Substrate dopant	Sn (n-type)
Substrate resistivity (Ω·cm)	0.007–0.042
Surface orientation	(001)
Backside finish	CMP
Wafer thickness (μm)	650
XRD FWHM (arcsec) *Not listed on delivery inspection sheet.	≤ 50

Remarks
1 There are cases in which the other side of OF is chipped (a maximum of around IF width).
2 These products must be used for research and development purposes only.
3 The substrates must not be used as a seed crystal.
4 The specifications are subject to change without notice.



Cross section of β-Ga_2O_3 epitaxial wafer



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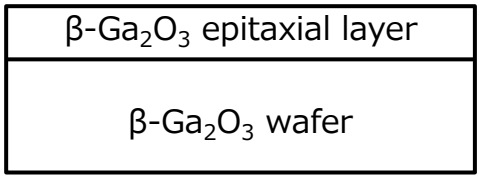
Standard specifications of 2 inch β-Ga_2O_3 epitaxial wafer (by HVPE)

Epitaxial layer

Items	Specifications
Dopant	Si+Cl[*1] (n-type)
Doping concentration (cm^{-3})	1×10^{16}
Thickness (μm) *Selectable in 1 μm increments.	5–10

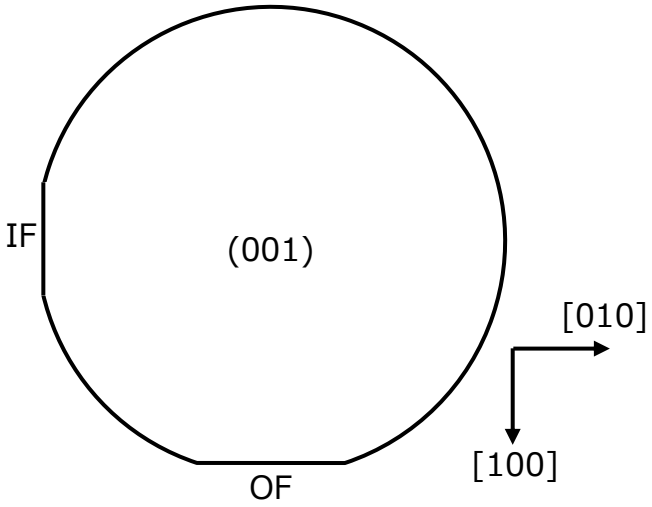
*1: Unintentionally-doped



Cross section of β-Ga_2O_3 epitaxial wafer

Epi-Wafer

Items	Specifications
Substrate dopant	Sn (n-type)
Substrate resistivity (Ω·cm)	0.007–0.042
Surface orientation	(001)
Backside finish	CMP
Wafer thickness (μm)	650
XRD FWHM (arcsec) *Not listed on delivery inspection sheet.	≤ 50



Orientation

Remarks
1 There are cases in which the other side of OF is chipped (a maximum of around IF width).
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